



## Dual N-Channel 150-V (D-S) MOSFET

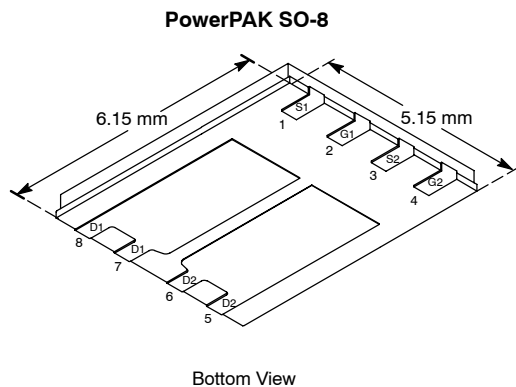
PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
150	0.150 @ $V_{GS} = 10$ V	3.3
	0.168 @ $V_{GS} = 6$ V	3.1

### FEATURES

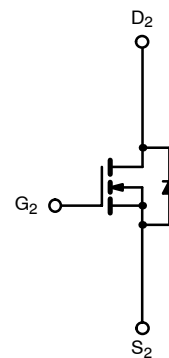
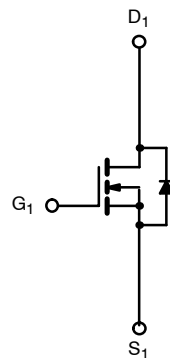
- TrenchFET® Power MOSFET
- New Low Thermal Resistance PowerPAK® Package
- Dual MOSFET for Space Savings
- PWM Optimized for Fast Switching
- Avalanche Rated

### APPLICATIONS

- Primary Side Switch



Ordering Information: Si7946DP-T1



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	10 secs	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	150		V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$			
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$I_D$	$T_A = 25^\circ\text{C}$	3.3	2.1	A
		$T_A = 70^\circ\text{C}$	2.6	1.7	
Pulsed Drain Current	$I_{DM}$	10			
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	2.9	1.2		
Single Avalanche Current	$I_{AS}$	L = 0.1 mH	9		
Single Avalanche Energy			$E_{AS}$	4	
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25^\circ\text{C}$	3.5	1.4	W
		$T_A = 70^\circ\text{C}$	2.2	0.9	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ sec	26	35	$^\circ\text{C/W}$
		Steady State	60	85	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	3.2	4.2		

Notes

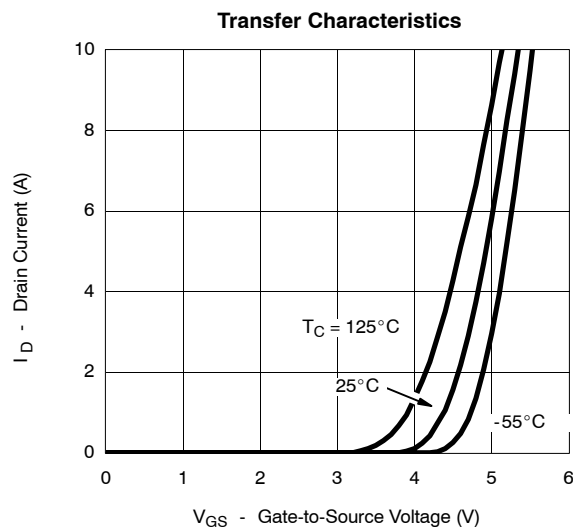
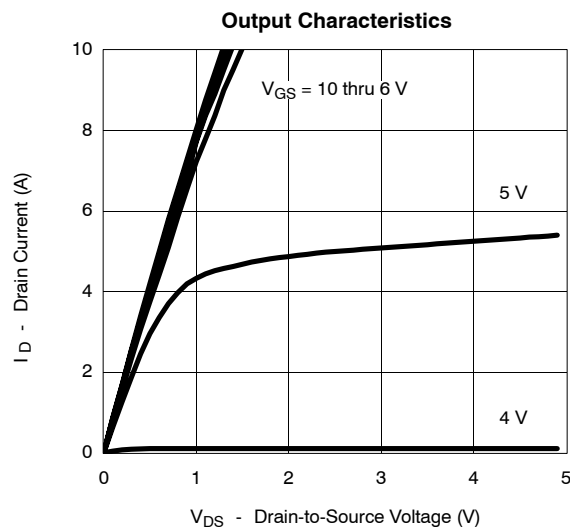
a. Surface Mounted on 1" x 1" FR4 Board.

**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2		4.0	V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	10			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.3 A		0.124	0.150	Ω
		V <sub>GS</sub> = 6 V, I <sub>D</sub> = 3.1 A		0.137	0.168	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 3.3 A		9		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 2.9 A, V <sub>GS</sub> = 0 V		0.87	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.3 A		12.6	20	nC
Gate-Source Charge	Q <sub>gs</sub>			2.8		
Gate-Drain Charge	Q <sub>gd</sub>			4.5		
Gate Resostance	R <sub>g</sub>	f = 1 MHz		3.5		Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 75 V, R <sub>L</sub> = 75 Ω I <sub>D</sub> ≅ 1 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 6 Ω		11	20	ns
Rise Time	t <sub>r</sub>			15	25	
Turn-Off Delay Time	t <sub>d(off)</sub>			30	45	
Fall Time	t <sub>f</sub>			20	30	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.9 A, di/dt = 100 A/μs		62	100	

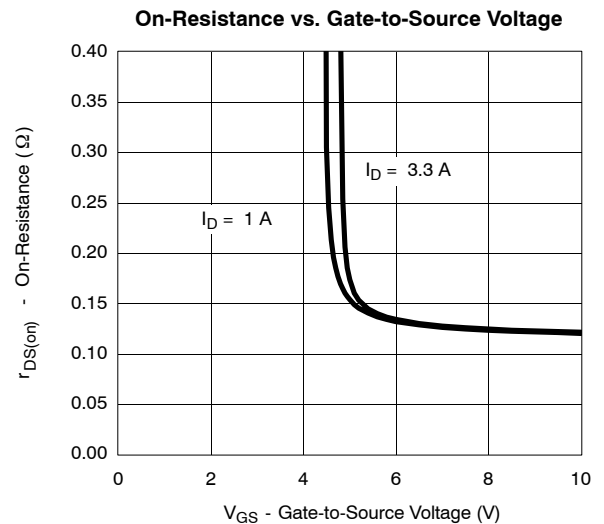
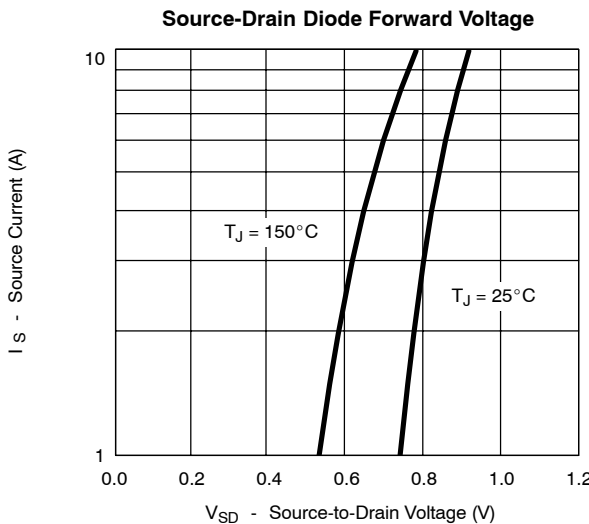
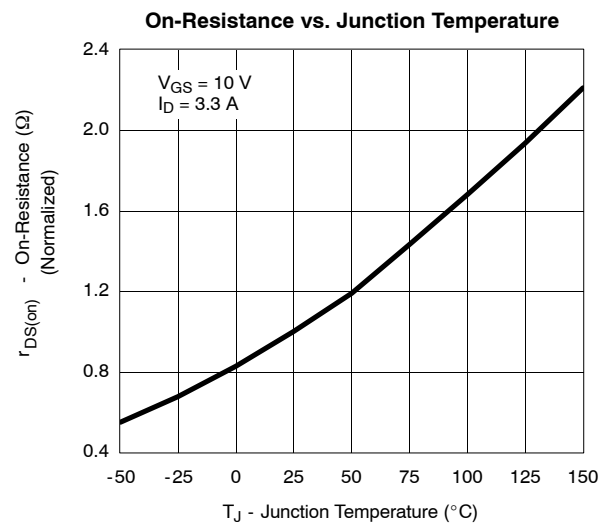
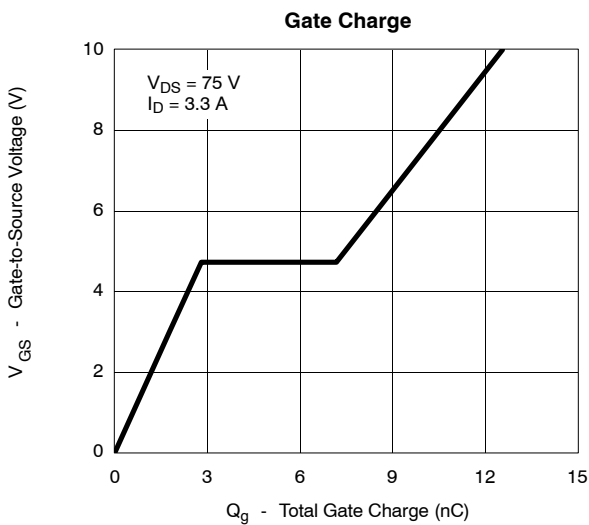
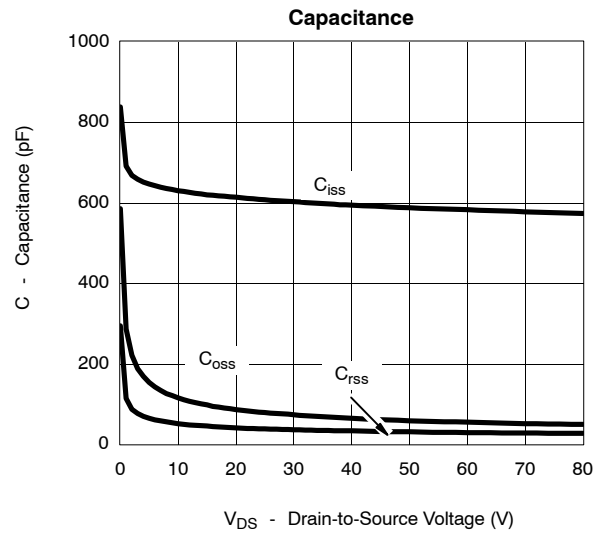
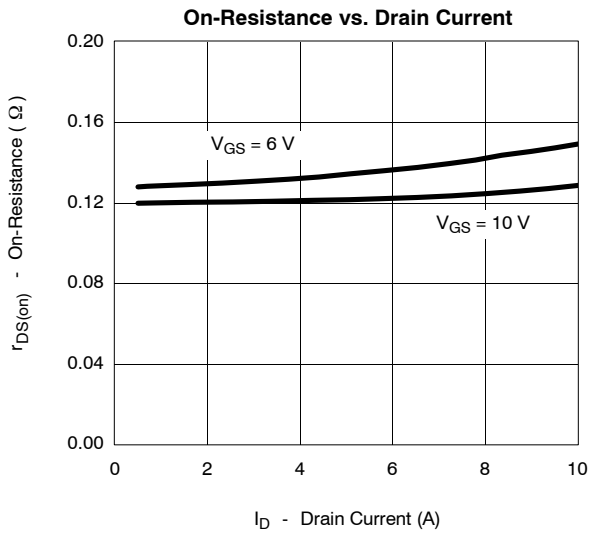
## Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.  
b. Guaranteed by design, not subject to production testing.

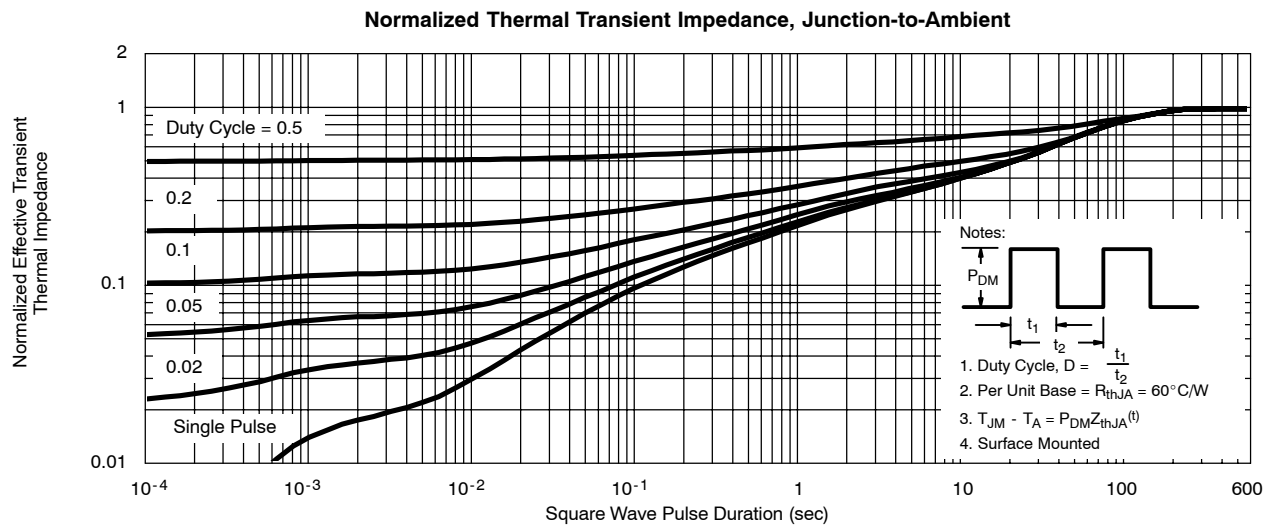
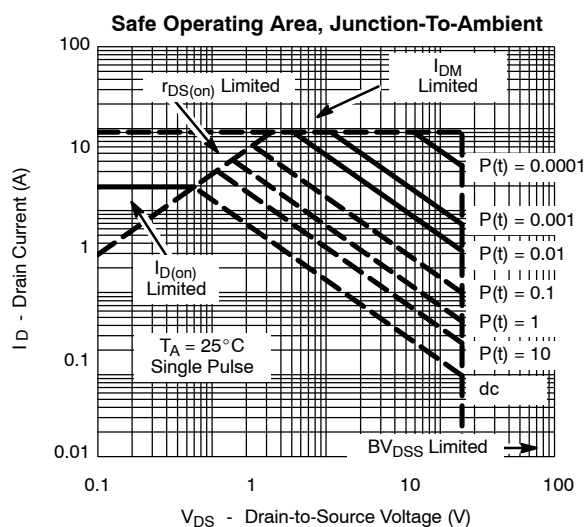
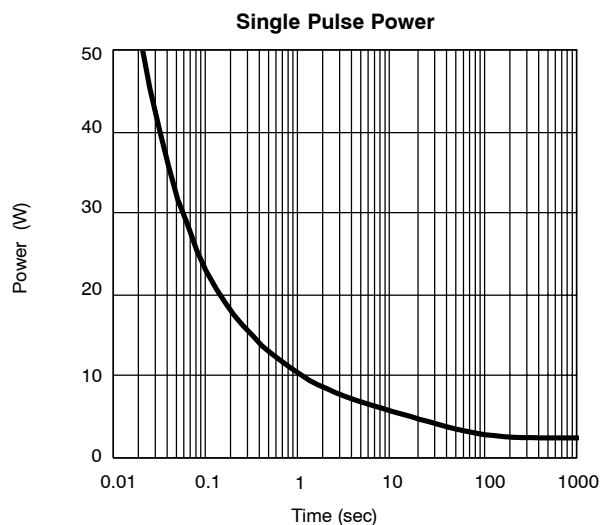
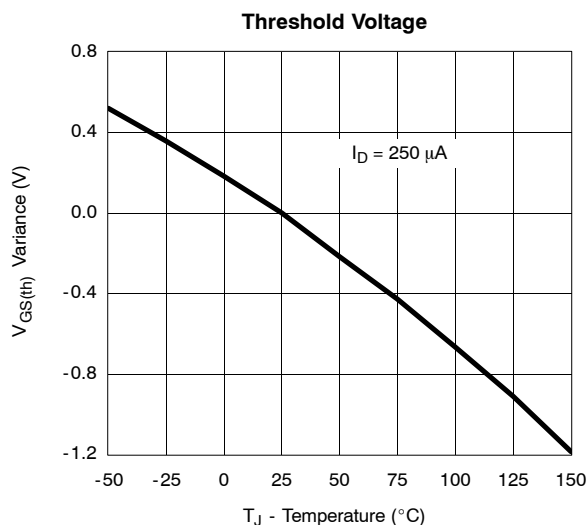
**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



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